

a wiring provided on said substrate;

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a pixel electrode provided on said substrate and superposed on said gate line with an insulator therebetween and superposed on said wiring with an insulator therebetween; and

at least one transistor provided on said substrate and connected with said gate line at a gate thereof and connected with said data line at one of source and drain thereof and connected with said pixel electrode at the other one of the source and drain wherein a capacitance between said pixel electrode and said gate line and a capacitance between said pixel electrode and said wiring are the same as each other.

5. (amended) An electro-optical device of an active matrix comprising:

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a gate line of n-th row provided on a substrate;

a gate line of (n+1)-th row provided on said substrate;

a data line of m-th column provided on said substrate;

a pixel electrode of n-th row and m-th column provided on said substrate and connected with said data line and said gate line of n-th row through corresponding at least one transistor; said pixel electrode being superposed on said data line with an insulator therebetween and superposed on said gate line of n-th row with an insulator therebetween; and

a pixel electrode of (n+1)-th row and m-th column provided on said substrate and connected with said data line and said gate line of (n+1)-th row through corresponding at least one transistor, said pixel electrode of (n+1)-th row and m-th column being superposed on said data line with an insulator therebetween and superposed on said gate line of (n+1)-th row with an insulator therebetween.

wherein said pixel electrode of n-th row and m-th column is provided on an opposite side of said data line to said pixel electrode of (n+1)-th row and m-th column.

B3 52 7 21. (amended) An electro-optical device of an active matrix comprising:
a gate line provided on a substrate;
a data line provided on said substrate;
an exclusive wiring provided on said substrate;
a pixel electrode provided on said substrate and superposed on said gate line
with an insulator therebetween and superposed on said wiring with an insulator
therebetween; and
at least one transistor provided on said substrate and connected with said
gate line at a gate thereof and connected with said data line at one of source and drain
thereof and connected with said pixel electrode at the other one of the source and drain
wherein a capacitance between said pixel electrode and said gate line and a capacitance
between said pixel electrode and said wiring are the same as each other.

22. (amended) An electro-optical device of an active matrix comprising:
a first gate line provided on a substrate;
a second gate line provided adjacent to said first gate line on said substrate;
a first pixel electrode provided on said substrate and connected with said
first gate line through at least one first transistor; and
a second pixel electrode provided on said substrate and connected with said
second gate line through at least one second transistor,
wherein said first pixel electrode is superposed on said first gate line with
an insulator therebetween and is superposed on said second gate line with another
insulator therebetween and wherein a difference between the area shared by said first gate
line and said pixel electrode and area shared by said second gate line and said pixel
electrode is not more than one tenth of sum of said area shared by said first gate line and
said pixel electrode and said area shared by said second gate line and said pixel electrode.